Quad Analog Switch/Quad Multiplexer

The MC14066B consists of four independent switches capable of controlling either digital or analog signals. This quad bilateral switch is useful in signal gating, chopper, modulator, demodulator and CMOS logic implementation.

The MC14066B is designed to be pin-for-pin compatible with the MC14016B, but has much lower ON resistance. Input voltage swings as large as the full supply voltage can be controlled via each independent control input.

Features

- Triple Diode Protection on All Control Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Linearized Transfer Characteristics
- Low Noise 12 nV/ $\sqrt{\text{Cycle}}$, f \geq 1.0 kHz typical
- Pin-for-Pin Replacement for CD4016, CD4016, MC14016B
- For Lower Ron, Use The HC4066 High-Speed CMOS Device
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Parameter	Value	Unit
DC Supply Voltage Range	-0.5 to +18.0	V
Input or Output Voltage Range (DC or Transient)	-0.5 to V _{DD} + 0.5	V
Input Current (DC or Transient) per Control Pin	±10	mA
Switch Through Current	±25	mA
Power Dissipation, per Package (Note 1)	500	mW
Ambient Temperature Range	-55 to +125	°C
Storage Temperature Range	-65 to +150	°C
Lead Temperature (8–Second Soldering)	260	°C
	DC Supply Voltage Range Input or Output Voltage Range (DC or Transient) Input Current (DC or Transient) per Control Pin Switch Through Current Power Dissipation, per Package (Note 1) Ambient Temperature Range Storage Temperature Range Lead Temperature	DC Supply Voltage Range

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Packages: –7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



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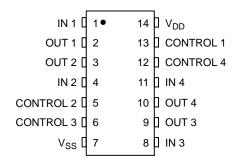






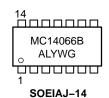
SOIC-14 D SUFFIX CASE 751A SOEIAJ-14 F SUFFIX CASE 965 TSSOP-14 DT SUFFIX CASE 948G

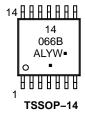
PIN ASSIGNMENT



MARKING DIAGRAMS







A = Assembly Location

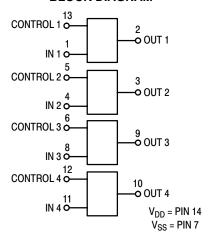
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

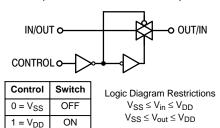
See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

BLOCK DIAGRAM



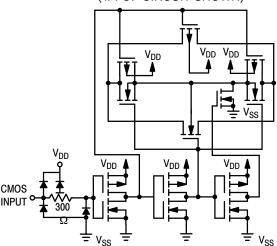
LOGIC DIAGRAM AND TRUTH TABLE

(1/4 OF DEVICE SHOWN)



CIRCUIT SCHEMATIC

(1/4 OF CIRCUIT SHOWN)



ELECTRICAL CHARACTERISTICS

				-5	5°C		25°C 125°C	5°C			
Characteristic	Symbol	V _{DD}	Test Conditions	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
SUPPLY REQUIREMENTS (\	/oltages Re	eferenc	ed to V _{EE})								
Power Supply Voltage Range	V _{DD}	_		3.0	18	3.0	-	18	3.0	18	V
Quiescent Current Per Package	I _{DD}	5.0 10 15	$\begin{split} & \text{Control Inputs:} \\ & V_{\text{in}} = V_{\text{SS}} \text{ or } V_{\text{DD}}, \\ & \text{Switch I/O: } V_{\text{SS}} \leq V_{\text{I/O}} \\ & \leq V_{\text{DD}}, \text{ and} \\ & \Delta V_{\text{switch}} \leq 500 \text{ mV} ^{(3)} \end{split}$	- - -	0.25 0.5 1.0	- - -	0.005 0.010 0.015	0.25 0.5 1.0	1 1 1	7.5 15 30	μΑ
Total Supply Current (Dynamic Plus Quiescent, Per Package	I _{D(AV)}	5.0 10 15	$\begin{split} T_A &= 25^{\circ}C \text{ only The} \\ &\text{channel component,} \\ &(V_{in} - V_{out})/R_{on}, \text{ is} \\ &\text{not included.)} \end{split}$		Typical	(0.2	7 μΑ/kHz) f 0 μΑ/kHz) f 6 μΑ/kHz) f	+ I _{DD}			μΑ
CONTROL INPUTS (Voltages	Reference	ed to V	_{SS})		-		-	-	_	-	-
Low-Level Input Voltage	V _{IL}	5.0 10 15	R _{on} = per spec, I _{off} = per spec	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	V
High-Level Input Voltage	V _{IH}	5.0 10 15	R _{on} = per spec, I _{off} = per spec	3.5 7.0 11		3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	٧
Input Leakage Current	I _{in}	15	V _{in} = 0 or V _{DD}	-	±0.1	-	±0.00001	±0.1	-	±1.0	μΑ
Input Capacitance	C _{in}	-		-	-	-	5.0	7.5	-	_	pF
SWITCHES IN AND OUT (Vo	Itages Refe	erencec	I to V _{SS})			•		•		•	
Recommended Peak-to-Peak Voltage Into or Out of the Switch	V _{I/O}	-	Channel On or Off	0	V _{DD}	0	_	V _{DD}	0	V _{DD}	V _{p-p}
Recommended Static or Dynamic Voltage Across the Switch (Note 3) (Figure 1)	ΔV _{switch}	-	Channel On	0	600	0	-	600	0	300	mV
Output Offset Voltage	V _{OO}	_	V _{in} = 0 V, No Load	-	-	-	10	_	-	_	μV
ON Resistance	R _{on}	5.0 10 15	$\begin{array}{l} \Delta V_{Switch} \leq 500 \text{ mV}^{(3)}, \\ V_{in} = V_{IL} \text{ or } V_{IH} \\ \text{ (Control), and } V_{in} = \\ 0 \text{ to } V_{DD} \text{ (Switch)} \end{array}$	- - -	800 400 220	- - -	250 120 80	1050 500 280	- - -	1200 520 300	Ω
ΔON Resistance Between Any Two Channels in the Same Package	ΔR_{on}	5.0 10 15		- - -	70 50 45	- - -	25 10 10	70 50 45	- - -	135 95 65	Ω
Off-Channel Leakage Current (Figure 6)	l _{off}	15	V _{in} = V _{IL} or V _{IH} (Control) Channel to Channel or Any One Channel	-	±100	-	±0.05	±100	-	±1000	nA
Capacitance, Switch I/O	C _{I/O}	_	Switch Off	_	-	_	10	15	_	_	pF
Capacitance, Feedthrough (Switch Off)	C _{I/O}	-		-	-	-	0.47	-	-	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labeled "Typ" is not to be used for design purposes, but is intended as an indication of the IC's potential performance.

For voltage drops across the switch (ΔV_{switch}) > 600 mV (> 300 mV at high temperature), excessive V_{DD} current may be drawn; i.e. the current out of the switch may contain both V_{DD} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded. (See first page of this data sheet.)

ELECTRICAL CHARACTERISTICS (Note 4) ($C_L = 50 \text{ pF}$, $T_A = 25^{\circ}\text{C}$ unless otherwise noted.)

Characteristic	Symbol	V _{DD} Vdc	Min	Typ (Note 5)	Max	Unit
Propagation Delay Times $V_{SS} = 0 \text{ Vdc}$ Input to Output (R _L = 10 k Ω) t_{PLH} , $t_{PHL} = (0.17 \text{ ns/pF}) C_L + 15.5 \text{ ns}$ t_{PLH} , $t_{PHL} = (0.08 \text{ ns/pF}) C_L + 6.0 \text{ ns}$	t _{PLH} , t _{PHL}	5.0 10 15	- -	20 10 7.0	40 20 15	ns
t_{PLH} , t_{PHL} = (0.06 ns/pF) C_L + 4.0 ns Control to Output (R_L = 1 k Ω) (Figure 2) Output "1" to High Impedance	t _{PHZ}	5.0 10 15	- - -	40 35 30	80 70 60	ns
Output "0" to High Impedance	t _{PLZ}	5.0 10 15	- - -	40 35 30	80 70 60	ns
High Impedance to Output "1"	t _{PZH}	5.0 10 15	- - -	60 20 15	120 40 30	ns
High Impedance to Output "0"	t _{PZL}	5.0 10 15	- - -	60 20 15	120 40 30	ns
Second Harmonic Distortion $V_{SS} = -5 \text{ Vdc}$ $(V_{in} = 1.77 \text{ Vdc}, \text{ RMS Centered @ 0.0 Vdc}, R_L = 10 \text{ k}\Omega, f = 1.0 \text{ kHz})$	-	5.0	-	0.1	-	%
$\begin{aligned} \text{Bandwidth (Switch ON) (Figure 3)} & \text{$V_{\text{SS}} = -5$ Vdc} \\ \text{$(R_{\text{L}} = 1 \text{ k}\Omega, 20 \text{ Log } (V_{\text{out}}/V_{\text{in}}) = -3$ dB, $C_{\text{L}} = 50$ pF,} \\ \text{$V_{\text{in}} = 5$ $V_{\text{p-p}}$} \end{aligned}$	-	5.0	-	65	-	MHz
	-	5.0	_	- 50	_	dB
Channel Separation (Figure 4) $ (V_{in} = 5 \ V_{p-p}, \ R_L = 1 \ k\Omega, \ f_{in} = 8.0 \ MHz) $ (Switch A ON, Switch B OFF) $ (S_{in} = 8.0 \ MHz) $	-	5.0	_	- 50	-	dB
Crosstalk, Control Input to Signal Output (Figure 5) $V_{SS} = -5 \text{ Vdc} \\ (R_1 = 1 \text{ k}\Omega, R_L = 10 \text{ k}\Omega, \text{Control } t_{TLH} = t_{THL} = 20 \text{ ns})$	_	5.0	-	300	-	mV _{p-p}

^{4.} The formulas given are for the typical characteristics only at 25°C.
5. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

TEST CIRCUITS

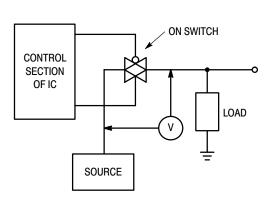


Figure 1. ΔV Across Switch

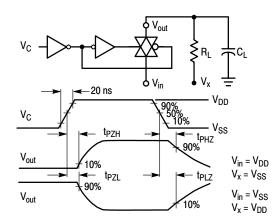


Figure 2. Turn-On Delay Time Test Circuit and Waveforms

 $V_C = V_{DD}$ FOR BANDWIDTH TEST $V_C = V_{SS}$ FOR FEEDTHROUGH TEST

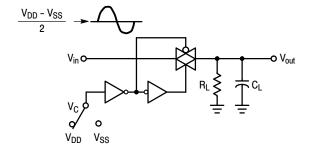


Figure 3. Bandwidth and Feedthrough Attenuation

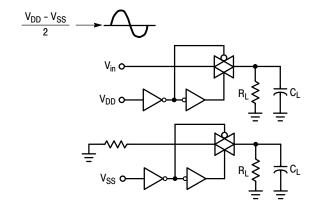


Figure 4. Channel Separation

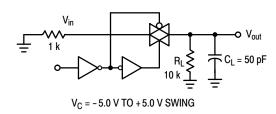


Figure 5. Crosstalk, Control to Output

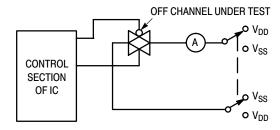


Figure 6. Off Channel Leakage

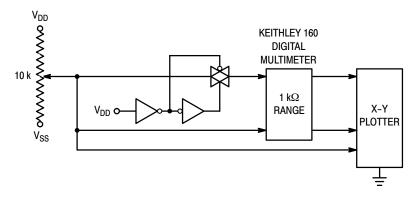


Figure 7. Channel Resistance (R_{ON}) Test Circuit

TYPICAL RESISTANCE CHARACTERISTICS

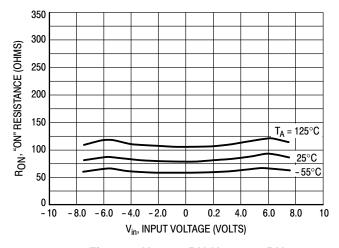


Figure 8. V_{DD} = 7.5 V, V_{SS} = - 7.5 V

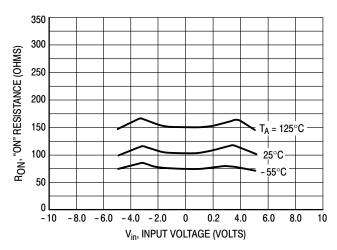


Figure 9. V_{DD} = 5.0 V, V_{SS} = - 5.0 V

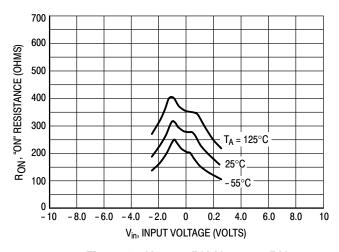


Figure 10. $V_{DD} = 2.5 \text{ V}, V_{SS} = -2.5 \text{ V}$

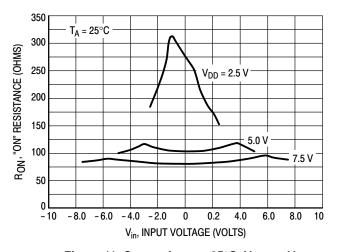


Figure 11. Comparison at 25°C, $V_{DD} = -V_{SS}$

APPLICATIONS INFORMATION

Figure A illustrates use of the Analog Switch. The 0-to-5 V digital control signal is used to directly control a 5 V peak-to-peak analog signal.

The digital control logic levels are determined by V_{DD} and V_{SS} . The V_{DD} voltage is the logic high voltage, the V_{SS} voltage is logic low. For the example, $V_{DD} = +5$ V = logic high at the control inputs; $V_{SS} = GND = 0$ V = logic low.

The maximum analog signal level is determined by V_{DD} and V_{SS} . The analog voltage must not swing higher than V_{DD} or lower than V_{SS} .

The example shows a 5 V peak-to-peak signal which allows no margin at either peak. If voltage transients above

 V_{DD} and/or below V_{SS} are anticipated on the analog channels, external diodes (D_x) are recommended as shown in Figure B. These diodes should be small signal types able to absorb the maximum anticipated current surges during clipping.

The *absolute* maximum potential difference between V_{DD} and V_{SS} is 18 V. Most parameters are specified up to 15 V which is the *recommended* maximum difference between V_{DD} and V_{SS} .

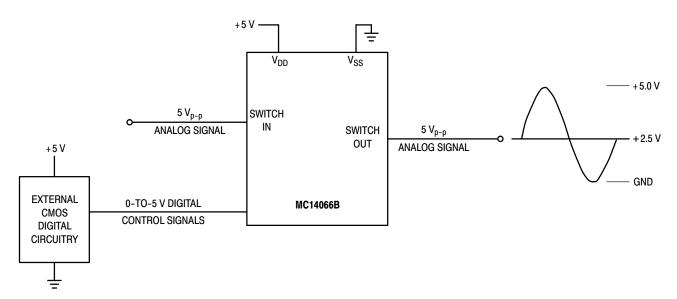


Figure A. Application Example

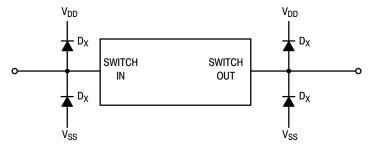


Figure B. External Germanium or Schottky Clipping Diodes

ORDERING INFORMATION

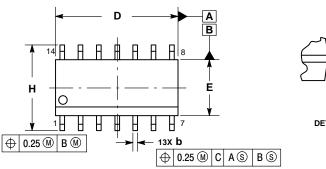
Device	Package	Shipping [†]
MC14066BDG	SOIC-14 (Pb-Free)	55 Units / Rail
NLV14066BDG*	SOIC-14 (Pb-Free)	55 Units / Rail
MC14066BDR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
NLV14066BDR2G*	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC14066BDTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLV14066BDTR2G*	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
MC14066BFELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

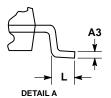
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

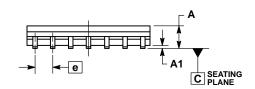
Capable.

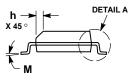
PACKAGE DIMENSIONS

SOIC-14 NB CASE 751A-03 ISSUE K









- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

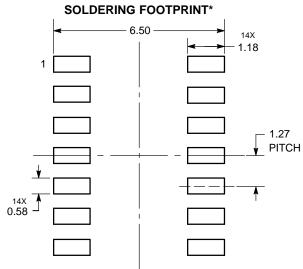
 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.

 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.

 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.35	1.75	0.054	0.068	
A1	0.10	0.25	0.004	0.010	
A3	0.19	0.25	0.008	0.010	
b	0.35	0.49	0.014	0.019	
D	8.55	8.75	0.337	0.344	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.019	
L	0.40	1.25	0.016	0.049	
М	0 °	7°	0 °	7°	

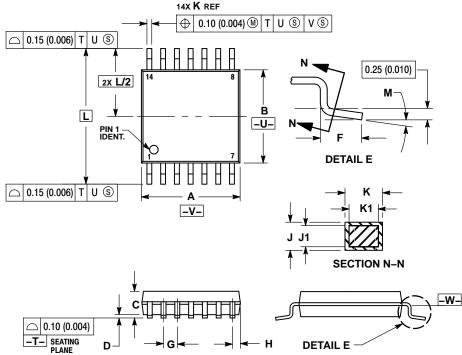


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G **ISSUE B**



NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

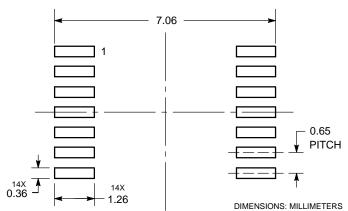
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Г	6.40	BSC	0.252	BSC	
М	0 °	8 °	0 °	8 °	

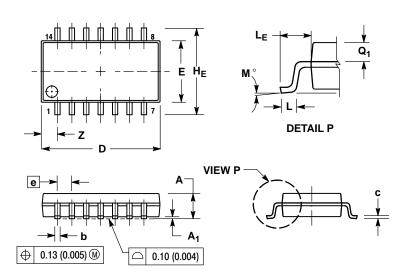
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOEIAJ-14 **CASE 965** ISSUE B



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- DIMENSIUNING AND Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE
 TOTAL AND ARE I. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- REFERENCE ONLY.

 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LΕ	1.10	1.50	0.043	0.059
М	0 °	10°	0 °	10°
Q1	0.70	0.90	0.028	0.035
Z		1.42		0.056

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